

Dmitry Yurasov

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Antimony segregation in Ge and formation of n-type selectively doped Ge films in molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	25
2	Impact of growth and annealing conditions on the parameters of Ge/Si(001) relaxed layers grown by molecular beam epitaxy. <i>Semiconductors</i> , 2015, 49, 1415-1420.	0.2	23
3	Light emission from Ge(Si)/SOI self-assembled nanoislands embedded in photonic crystal slabs of various periods with and without cavities. <i>Semiconductor Science and Technology</i> , 2019, 34, 024003.	1.0	22
4	Optical monitoring of technological parameters during molecular-beam epitaxy. <i>Semiconductors</i> , 2012, 46, 1471-1475.	0.2	18
5	Critical thickness for the Stranski-Krastanov transition treated with the effect of segregation. <i>Semiconductors</i> , 2008, 42, 563-570.	0.2	17
6	Recovery of SIMS depth profiles with account for nonstationary effects. <i>Applied Surface Science</i> , 2014, 307, 33-41.	3.1	13
7	Secondary cluster ions Ge_2^+ and Ge_3^+ for improving depth resolution of SIMS depth profiling of GeSi/Si heterostructures. <i>Semiconductors</i> , 2010, 44, 401-404.	0.2	10
8	TOF-SIMS 5 instrument sensitivity to matrix elements in GeSi Layers: Analysis based on recording of complex secondary ions. <i>Journal of Surface Investigation</i> , 2011, 5, 591-594.	0.1	9
9	Selective etching of Si, SiGe, Ge and its usage for increasing the efficiency of silicon solar cells. <i>Semiconductors</i> , 2017, 51, 1542-1546.	0.2	9
10	Influence of elastic strains in sublayers on the critical thickness of the Stranski-Krastanow transition for the GeSi/Si(001) system. <i>Journal of Surface Investigation</i> , 2009, 3, 548-553.	0.1	7
11	A new approach to the diagnostics of nanoislands in Ge_xSi_{1-x} /Si heterostructures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2014, 40, 601-605.	0.2	7
12	Influence of thermal annealing on the electrical and luminescent properties of heavily Sb-doped Ge/Si(001) layers. <i>Semiconductor Science and Technology</i> , 2018, 33, 124019.	1.0	7
13	Spin pump induced inverse spin Hall effect observed in Bi-doped n -type Si. <i>Physical Review B</i> , 2020, 101, .	1.1	7
14	Barrier-height modification in Schottky silicon diodes with highly doped 3D and 2D layers. <i>Semiconductors</i> , 2012, 46, 1358-1361.	0.2	6
15	Method for taking into account the shift parameter in the deconvolution of the depth composition distribution of semiconductor structures from SIMS depth profiles. <i>Semiconductors</i> , 2012, 46, 1481-1486.	0.2	6
16	Transition from planar to island growth mode in SiGe structures fabricated on SiGe/Si(001) strain-relaxed buffers. <i>Applied Physics Letters</i> , 2012, 101, 151601.	1.5	5
17	Quantitative calibration and germanium SIMS depth profiling in Ge_xSi_{1-x} /Si heterostructures. <i>Semiconductors</i> , 2014, 48, 1109-1117.	0.2	5
18	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. <i>Semiconductors</i> , 2017, 51, 663-666.	0.2	5

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19	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. <i>Semiconductors</i> , 2017, 51, 1477-1480.	0.2	4
20	Transition from the two- to three-dimensional growth of Ge films upon deposition onto relaxed SiGe/Si(001) buffer layers. <i>Semiconductors</i> , 2013, 47, 427-432.	0.2	3
21	Use of related parameters in X-ray diffraction analysis of multilayer structures with allowance for the layer growth time. <i>Technical Physics</i> , 2014, 59, 402-406.	0.2	3
22	Growth of light-emitting SiGe heterostructures on strained silicon-on-insulator substrates with a thin oxide layer. <i>Semiconductors</i> , 2015, 49, 1104-1110.	0.2	3
23	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , 2018, 52, 1547-1550.	0.2	3
24	Formation and Properties of Locally Tensile Strained Ge Microstructures for Silicon Photonics. <i>Semiconductors</i> , 2018, 52, 1442-1447.	0.2	3
25	Influence of Annealing on the Properties of Ge:Sb/Si(001) Layers with an Antimony Concentration Above Its Equilibrium Solubility in Germanium. <i>Semiconductors</i> , 2019, 53, 882-886.	0.2	3
26	Study of the transition of the epitaxial Ge film from layer-to-layer to three-dimensional growth in heterostructures with strained SiGe sublayers. <i>Semiconductors</i> , 2010, 44, 519-524.	0.2	2
27	Direct comparison of superlattice periods measured with X-ray diffractometry and optical interferometry. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2011, 75, 40-43.	0.1	2
28	Layer-by-layer analysis of structures containing $\hat{\Gamma}$ -layers by secondary ion mass spectrometry taking into account the TOF.SIMS-5 depth resolution function. <i>Journal of Surface Investigation</i> , 2012, 6, 574-577.	0.1	2
29	New approach to the X-ray diffraction analysis of test structures during flow calibration in epitaxial growth reactors. <i>Journal of Surface Investigation</i> , 2012, 6, 494-497.	0.1	2
30	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , 2015, 41, 648-650.	0.2	2
31	Nonlinear calibration curves in secondary ion mass spectrometry for quantitative analysis of gesi heterostructures with nanoclusters. <i>Technical Physics Letters</i> , 2016, 42, 243-247.	0.2	2
32	Enhancement of the Luminescence Signal from Self-Assembled Ge(Si) Nanoislands due to Interaction with the Modes of Two-Dimensional Photonic Crystals. <i>Semiconductors</i> , 2020, 54, 975-981.	0.2	2
33	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , 2020, 127, 165701.	1.1	2
34	Enhancing the photoluminescence response from thick Ge-on-Si layers using the photonic crystals. <i>Journal Physics D: Applied Physics</i> , 0, , .	1.3	2
35	Method of selective doping of silicon by segregating impurities. <i>Technical Physics Letters</i> , 2011, 37, 824-826.	0.2	1
36	Antimony segregation in stressed SiGe heterostructures grown by molecular beam epitaxy. <i>Semiconductors</i> , 2013, 47, 1481-1484.	0.2	1

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37	Influence of surface roughness on a change in the growth mode from two-dimensional to three-dimensional for strained SiGe heterostructures. <i>Semiconductors</i> , 2016, 50, 1630-1634.	0.2	1
38	Electroluminescence of structures with self-assembled Ge(Si) nanoislands confined between strained Si layers. <i>Semiconductors</i> , 2016, 50, 1657-1661.	0.2	1
39	A New Limitation of the Depth Resolution in TOF-SIMS Elemental Profiling: the Influence of a Probing Ion Beam. <i>Technical Physics Letters</i> , 2018, 44, 320-323.	0.2	1
40	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , 2019, 53, 1318-1323.	0.2	1
41	Locally Strained Ge/SOI Structures with an Improved Heat Sink as an Active Medium for Silicon Optoelectronics. <i>Semiconductors</i> , 2019, 53, 1324-1328.	0.2	1
42	Influence of the Growth Conditions and Doping Level on the Luminescence Kinetics of Ge:Sb Layers Grown on Silicon. <i>Semiconductors</i> , 2020, 54, 811-816.	0.2	1
43	Influence of irradiation by Swift Heavy Ions (SHI) on electronic magnetotransport in Sb δ -layer in silicon. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2022, 138, 115047.	1.3	1
44	Comparison of III-V Heterostructures Grown on Ge/Si, Ge/SOI, and GaAs. <i>Semiconductors</i> , 2022, 56, 122-133.	0.2	1
45	Plastic relaxation in GeSi layers on Si (001) and Si (115) substrates. <i>Semiconductors</i> , 2015, 49, 19-22.	0.2	0
46	Hodographs in diode-structure diagnostics. <i>Semiconductors</i> , 2015, 49, 1443-1447.	0.2	0
47	On the radiative recombination and tunneling of charge carriers in SiGe/Si heterostructures with double quantum wells. <i>Semiconductors</i> , 2016, 50, 1604-1608.	0.2	0
48	Antimony segregation in Si layers grown by molecular beam epitaxy on Si wafers with different crystallographic orientations. <i>Semiconductors</i> , 2017, 51, 1552-1556.	0.2	0
49	Stimulated Emission in the 1.3-1.5 μ m Spectral Range from AlGaInAs Quantum Wells in Hybrid Light-Emitting III-V Heterostructures on Silicon Substrates. <i>Semiconductors</i> , 2018, 52, 1495-1499.	0.2	0
50	Stimulated Emission at 1.3- μ m Wavelength in Metamorphic InGaAs/InGaAsP Structure with Quantum Wells Grown on Ge/Si(001) Substrate. <i>Technical Physics Letters</i> , 2018, 44, 735-738.	0.2	0
51	Photoluminescence Enhancement Phenomena in Photonic Crystal Slabs Formed on Si Structures with the Self-Assembled Ge Nanoislands. , 2019, , .		0
52	Photoluminescence Enhancement Phenomena in Photonic Crystal Slabs Formed on Si Structures with the Self-Assembled Ge Nanoislands. , 2019, , .		0
53	Formation and Optical Properties of Locally Strained Ge Microstructures Embedded into Cavities. <i>Semiconductors</i> , 2021, 55, 531.	0.2	0